

30V 0.7mohm N-channel SGT MOSFET  
AKG3N007GAL

Description:

This N channel SGT MOSFET has been designed for automotive applications and manufactured in IATF16949 certified facilities.

Features:

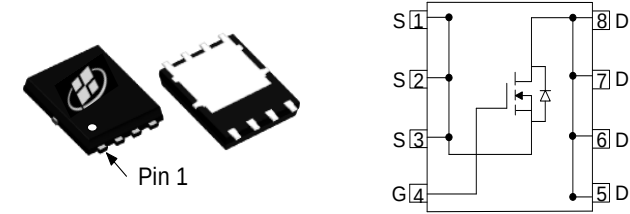
- Low  $R_{DS(ON)}$
- RoHS compliant
- Halogen-free

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

| Parameter                                | Value | Unit      |
|------------------------------------------|-------|-----------|
| $V_{DS}$                                 | 30    | V         |
| $R_{DS(ON), max} @ V_{GS} = 10\text{ V}$ | 0.7   | $m\Omega$ |
| $I_D$                                    | 288   | A         |



Ordering Information:

| Ordering Code | Package Type | Marking Code | Form      | Packing       |
|---------------|--------------|--------------|-----------|---------------|
| AKG3N007GAL   | PDFN5X6      | G3N007GAL    | Tape Reel | 5000 per reel |

Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise noted)

| Symbol                            | Parameter                                                              | Value       | Units |
|-----------------------------------|------------------------------------------------------------------------|-------------|-------|
| V <sub>DS</sub>                   | Drain - Source Voltage                                                 | 30          | V     |
| I <sub>D</sub>                    | Drain Current - Continuous (T <sub>C</sub> = 25°C) <sup>(Note 1)</sup> | 288         | A     |
|                                   | Drain Current - Continuous (T <sub>C</sub> = 100°C)                    | 182         | A     |
| I <sub>DM</sub>                   | Drain Current - Pulsed <sup>(Note 2)</sup>                             | 880         | A     |
| V <sub>GS</sub>                   | Gate - Source Voltage                                                  | ± 20        | V     |
| E <sub>AS</sub>                   | Single Pulsed Avalanche Energy <sup>(Note 3)</sup>                     | 702         | mJ    |
| P <sub>D</sub>                    | Power Dissipation (T <sub>C</sub> = 25°C)                              | 96          | W     |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                                | -55 to +150 | °C    |

Thermal Characteristics

| Symbol           | Parameter                                                                     | Value | Units |
|------------------|-------------------------------------------------------------------------------|-------|-------|
| R <sub>θJC</sub> | Thermal Resistance, Junction - to - Case, Steady State                        | 1.3   | °C/W  |
| R <sub>θJA</sub> | Thermal Resistance, Junction - to - Ambient, Steady State <sup>(Note 4)</sup> | 45    | °C/W  |

Notes:

- 1. The max drain current rating is silicon limited
- 2. Repetitive Rating: Pulse width limited by maximum junction temperature
- 3. L = 0.5 mH, V<sub>DD</sub> = 40 V, I<sub>AS</sub> = 53 A, R<sub>g</sub> = 50 Ω, Starting T<sub>J</sub> = 25 °C
- 4. Mount on minimum PCB layout

**Electrical Characteristics** ( $T_j = 25^\circ\text{C}$  unless otherwise noted)

| Symbol                                                   | Parameter                                       | Test Conditions                                                                                     | Min | Typ  | Max  | Units |
|----------------------------------------------------------|-------------------------------------------------|-----------------------------------------------------------------------------------------------------|-----|------|------|-------|
| Static Characteristics                                   |                                                 |                                                                                                     |     |      |      |       |
| V <sub>(BR)DSS</sub>                                     | Drain - Source Breakdown Voltage                | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1mA                                                         | 30  |      |      | V     |
| I <sub>DSS</sub>                                         | Zero Gate Voltage Drain Current                 | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V,                                                      |     |      | 1    | μA    |
| I <sub>GSS</sub>                                         | Gate Leakage Current                            | V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V                                                     |     |      | ±100 | nA    |
| V <sub>GS(th)</sub>                                      | Gate Threshold voltage                          | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                         | 1   | 1.7  | 3    | V     |
| R <sub>DS(ON)</sub>                                      | Drain - Source on - state resistance            | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A                                                       |     | 0.55 | 0.7  | mΩ    |
|                                                          |                                                 | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A                                                      |     | 0.8  | 1    | mΩ    |
| Dynamic Characteristics                                  |                                                 |                                                                                                     |     |      |      |       |
| C <sub>iss</sub>                                         | Input Capacitance                               | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,<br>f = 1 MHz                                         |     | 8334 |      | pF    |
| C <sub>oss</sub>                                         | Output Capacitance                              |                                                                                                     |     | 2849 |      | pF    |
| C <sub>rss</sub>                                         | Reverse Transfer Capacitance                    |                                                                                                     |     | 648  |      | pF    |
| R <sub>g</sub>                                           | Gate Resistance                                 | f = 1 MHz                                                                                           |     | 2.5  |      | Ω     |
| Switching Characteristics                                |                                                 |                                                                                                     |     |      |      |       |
| t <sub>d(on)</sub>                                       | Turn On Delay Time                              | V <sub>DD</sub> = 15 V , R <sub>L</sub> = 0.75 Ω,<br>V <sub>GS</sub> = 10 V, R <sub>G</sub> = 6.8 Ω |     | 13   |      | ns    |
| t <sub>r</sub>                                           | Rise Time                                       |                                                                                                     |     | 41   |      | ns    |
| t <sub>d(off)</sub>                                      | Turn Off Delay Time                             |                                                                                                     |     | 85   |      | ns    |
| t <sub>f</sub>                                           | Fall Time                                       |                                                                                                     |     | 60   |      | ns    |
| Q <sub>g</sub>                                           | Total Gate Charge                               | V <sub>DD</sub> = 15 V , I <sub>D</sub> = 20 A,<br>V <sub>GS</sub> = 10 V                           |     | 140  |      | nC    |
| Q <sub>gs</sub>                                          | Gate - Source Charge                            |                                                                                                     |     | 24   |      | nC    |
| Q <sub>gd</sub>                                          | Gate - Drain Charge                             |                                                                                                     |     | 34   |      | nC    |
| Drain - Source Diode Characteristics and Maximum Ratings |                                                 |                                                                                                     |     |      |      |       |
| I <sub>S</sub>                                           | Maximum Continuous Body - Diode Forward Current |                                                                                                     |     |      | 288  | A     |
| I <sub>SM</sub>                                          | Maximum Pulsed Body - Diode Forward Current     |                                                                                                     |     |      | 880  | A     |
| V <sub>SD</sub>                                          | Diode Forward Voltage                           | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1 A                                                         |     | 0.63 |      | V     |
| t <sub>rr</sub>                                          | Reverse recovery time                           | V <sub>DD</sub> = 15 V, I <sub>D</sub> = 15 A,<br>di/dt = 100 A/μs                                  |     | 75   |      | ns    |
| Q <sub>rr</sub>                                          | Reverse recovery charge                         |                                                                                                     |     | 95   |      | nC    |
| I <sub>rrm</sub>                                         | Peak Reverse Recovery Current                   |                                                                                                     |     | 2.1  |      | A     |

Electrical Characteristics Diagrams

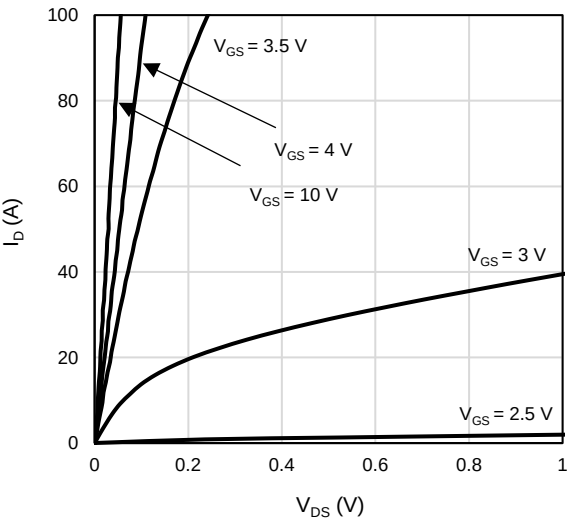


Figure 1: On-Region Characteristics

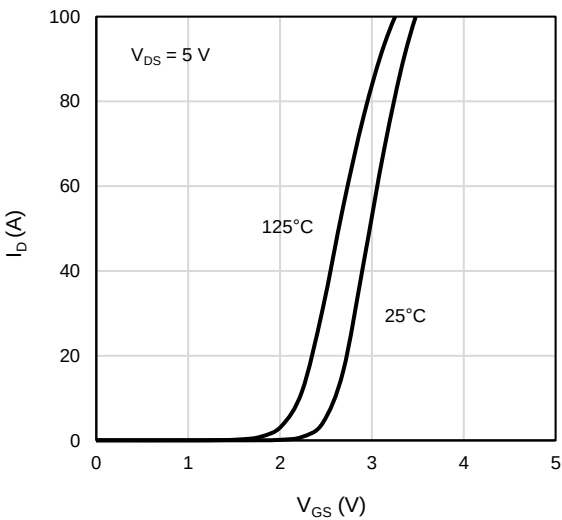


Figure 2: Transfer Characteristics

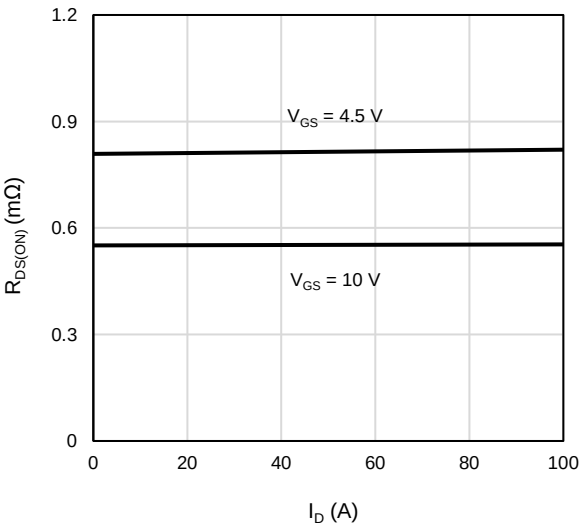


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

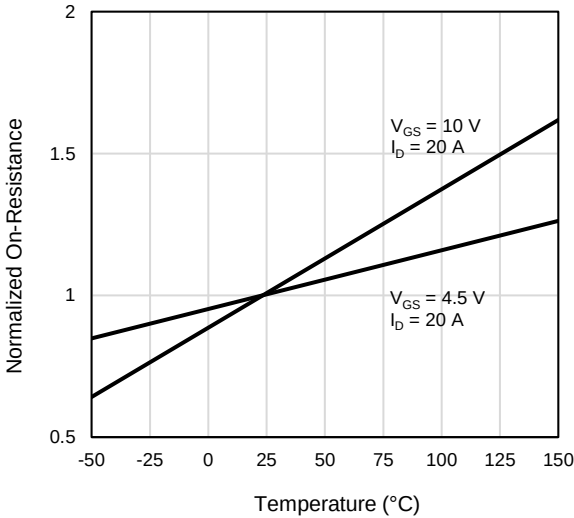


Figure 4: On-Resistance vs. Junction Temperature

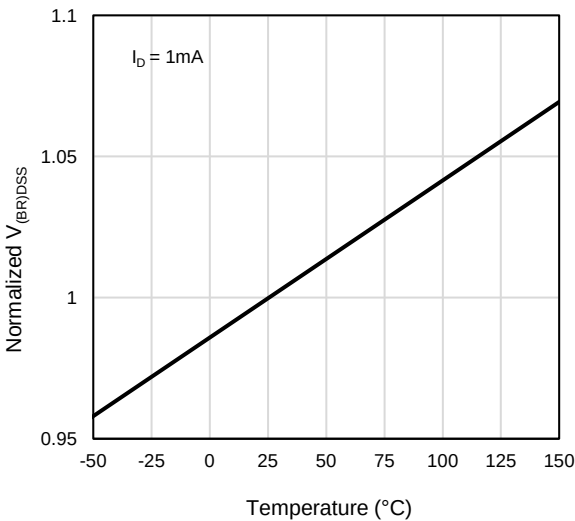


Figure 5: Breakdown Voltage vs. Junction Temperature

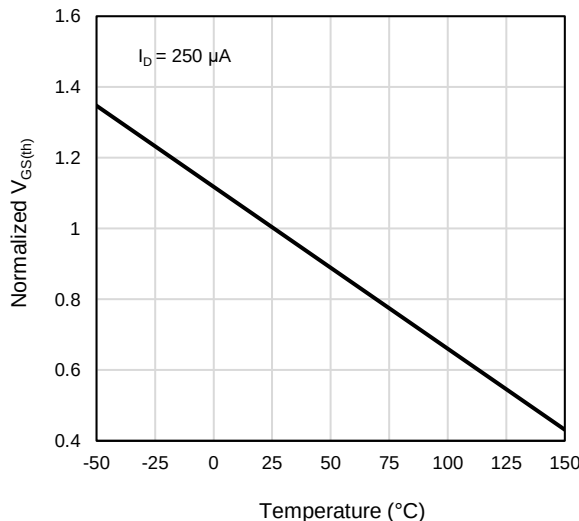
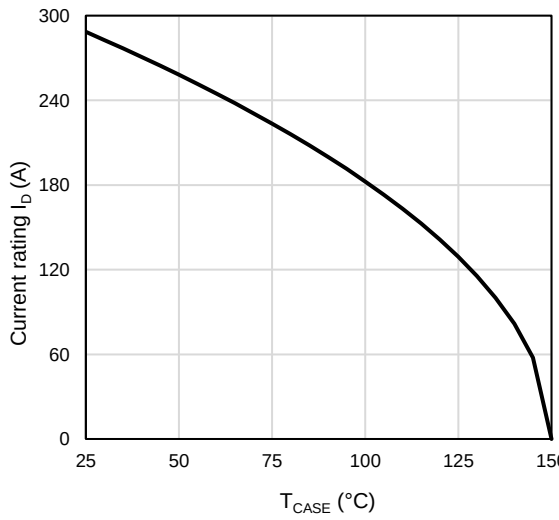
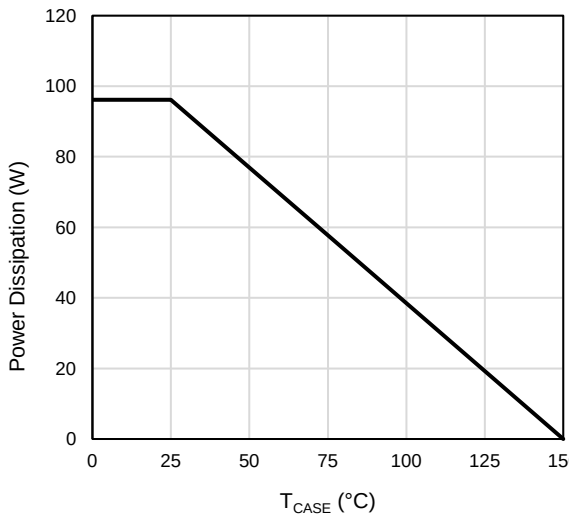
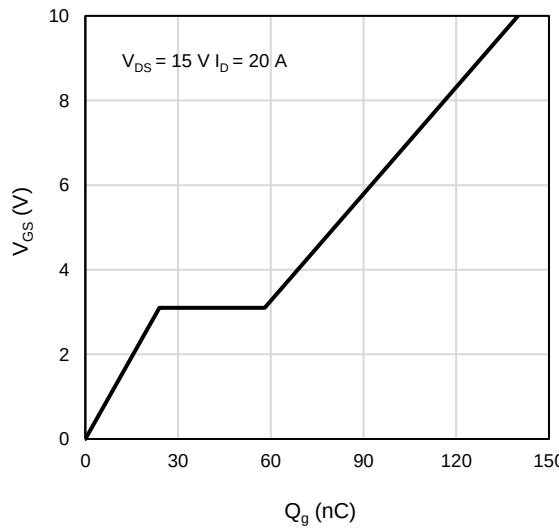
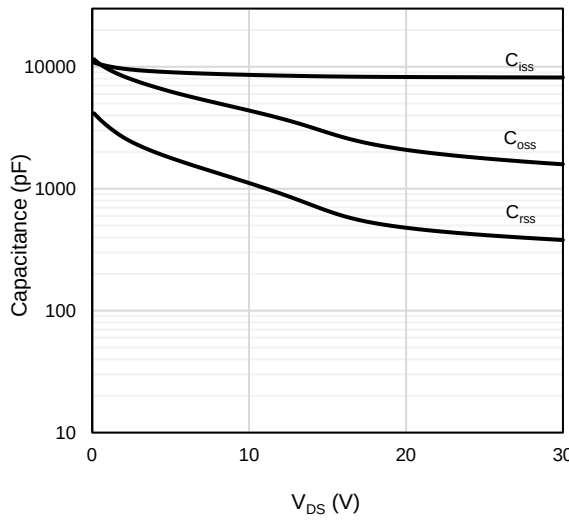
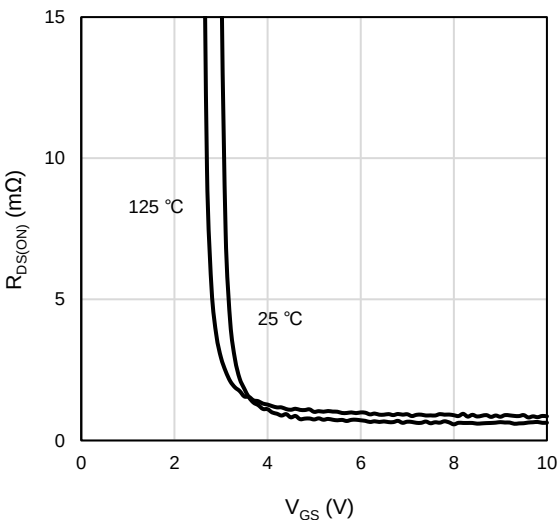
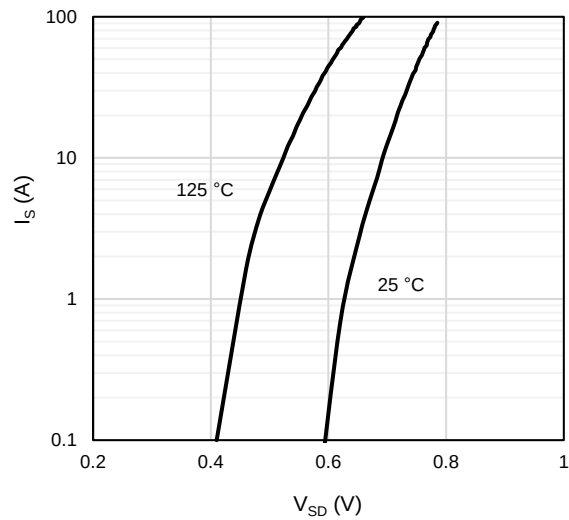


Figure 6: Threshold Voltage vs. Junction Temperature



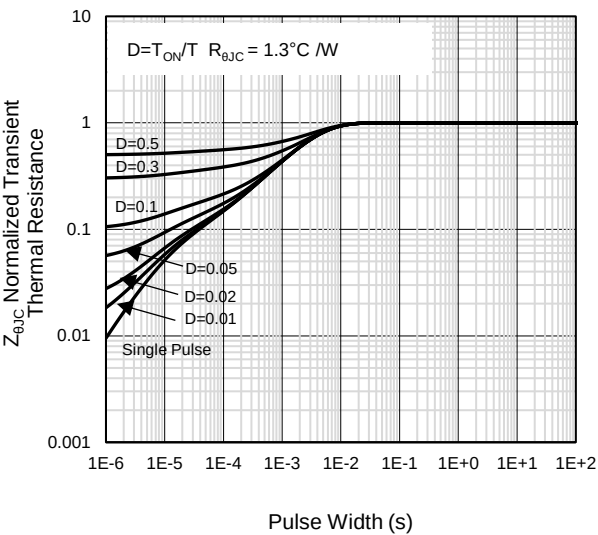


Figure 13: Normalized Maximum Transient Thermal Impedance

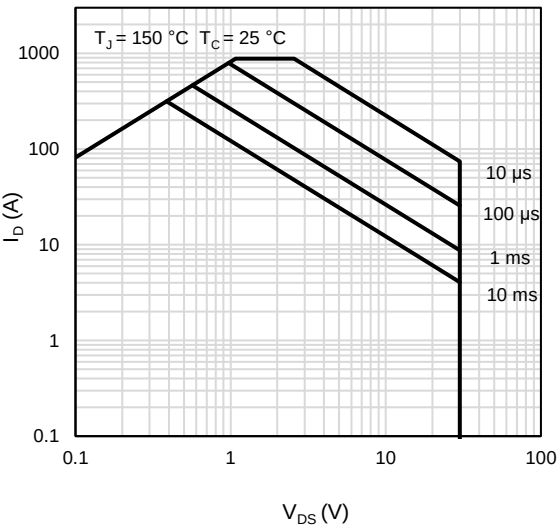
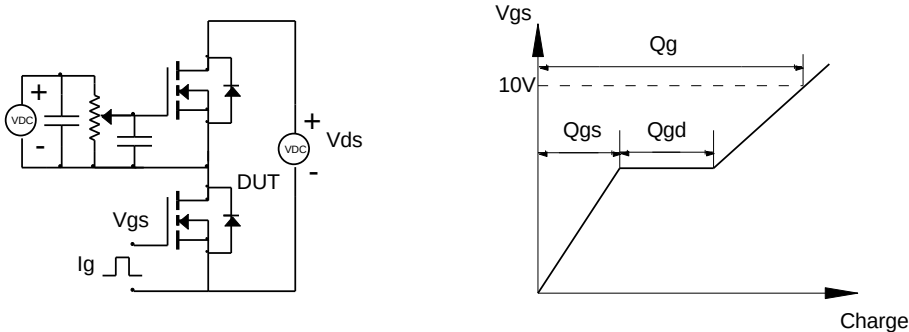


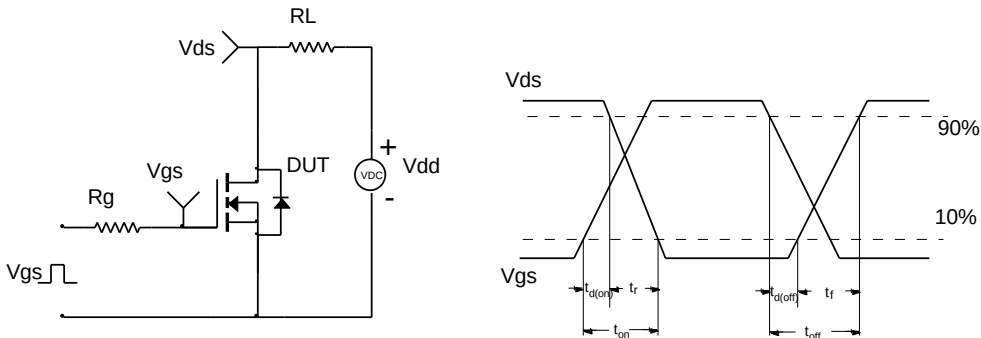
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

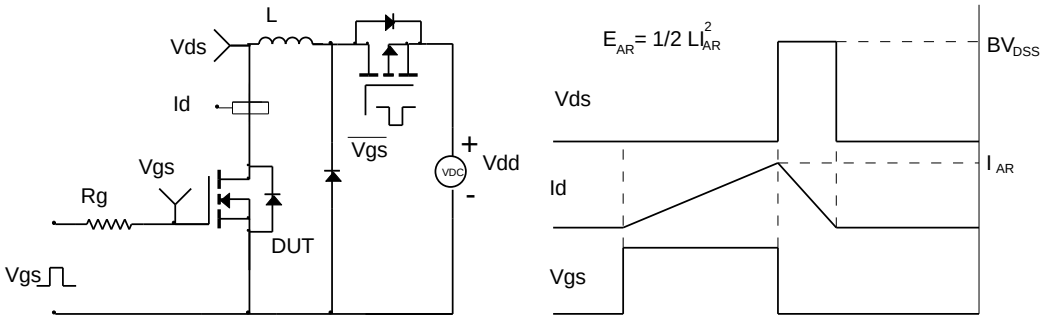
Gate Charge Test Circuit & Waveform



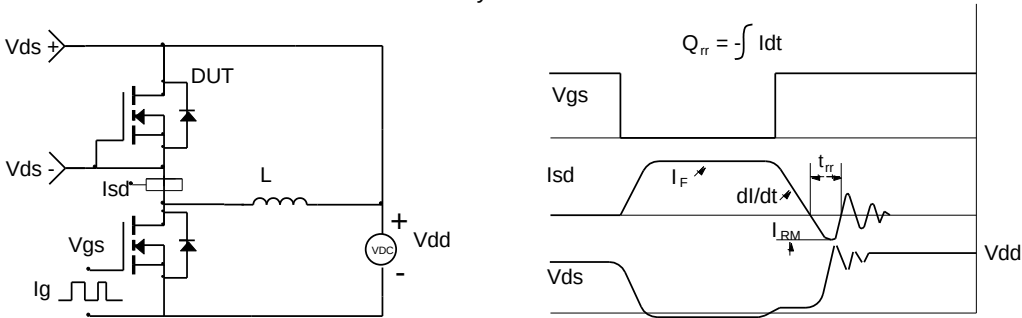
Resistive Switching Test Circuit & Waveforms



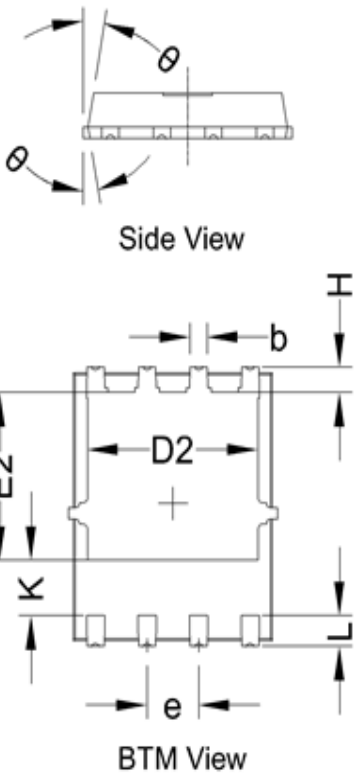
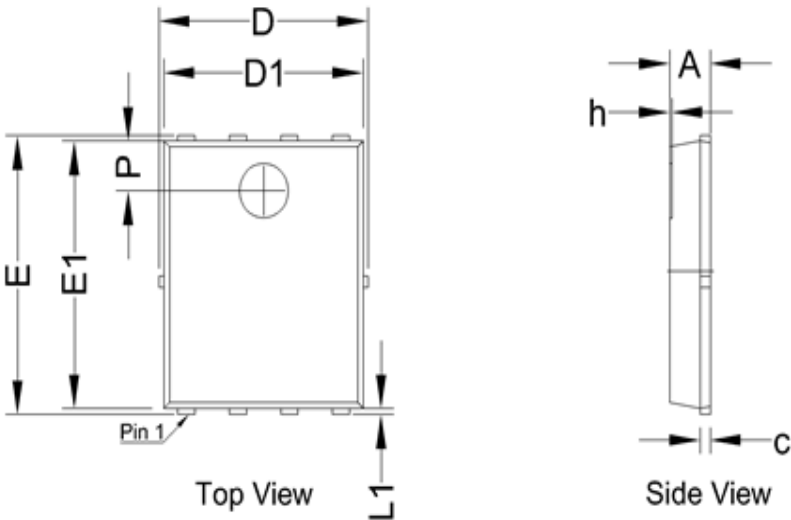
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outlines

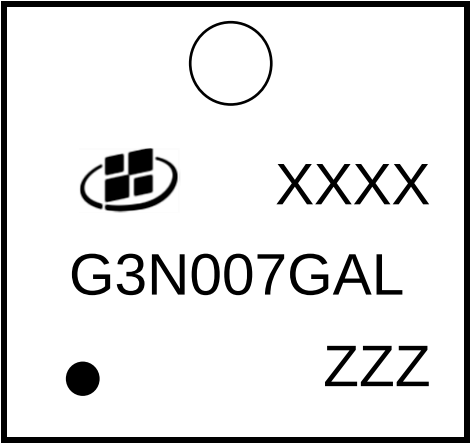


| SYMBOL | MIN     | NOM  | MAX  |
|--------|---------|------|------|
| A      | 0.90    | 1.00 | 1.10 |
| b      | 0.32    | 0.42 | 0.52 |
| c      | 0.21    | 0.25 | 0.34 |
| D      | 5.00    | 5.15 | 5.30 |
| D1     | 4.80    | 4.90 | 5.00 |
| D2     | 4.10    | 4.20 | 4.30 |
| e      | 1.27BSC |      |      |
| E      | 6.00    | 6.15 | 6.30 |
| E1     | 5.80    | 5.90 | 6.00 |
| E2     | 3.60    | 3.70 | 3.80 |
| H      | 0.45    | 0.55 | 0.65 |
| h      | —       | —    | 0.10 |
| K      | 1.17    | —    | —    |
| L      | 0.58    | 0.68 | 0.78 |
| L1     | 0.05    | 0.13 | 0.21 |
| Θ      | 8°      | 10°  | 12°  |
| P      | 1.05    | 1.10 | 1.15 |

Unit in mm



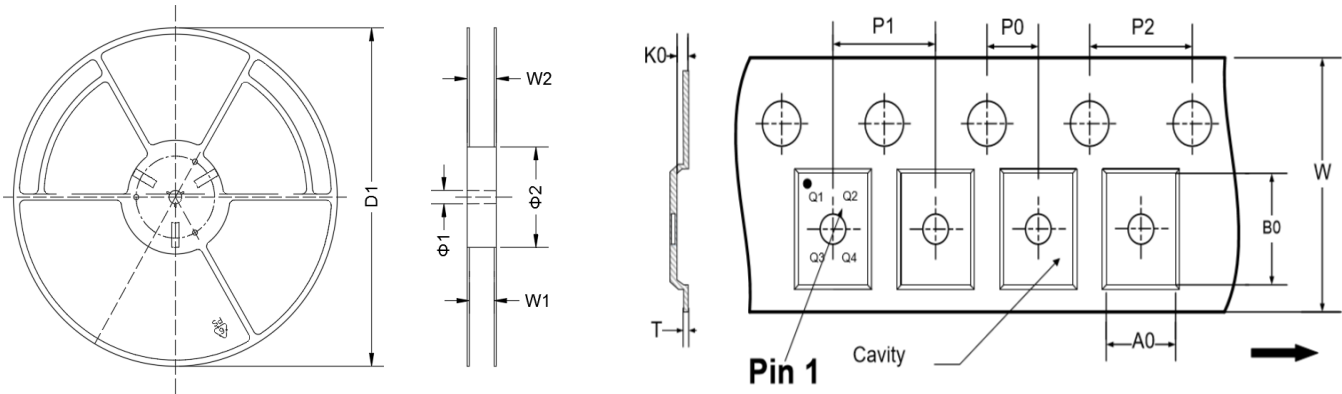
Marking Information



Note:  
G3N007GAL = Product Name Code  
XXXX = Date code  
ZZZ  
Contact ALKAIDSEMI sales for detail information

Tape & Reel Information

REEL DIMENSIONS



| DIMENSIONS(Unit:mm) |     |      |      |      |      |      |     |      |               |          |
|---------------------|-----|------|------|------|------|------|-----|------|---------------|----------|
| Tape                | P0  | P1   | P2   | W    | A0   | B0   | K0  | T    | Pin1 Quadrant | Material |
|                     | 2   | 8    | 4    | 12   | 6.45 | 5.45 | 1.2 | 0.25 | Q2            | PC       |
| DIMENSIONS(Unit:mm) |     |      |      |      |      |      |     |      |               |          |
| Reel                | D1  | W1   | W2   | Φ1   | Φ2   |      |     |      |               | Material |
|                     | 330 | 12.4 | 18.4 | 13.5 | 100  |      |     |      |               | Hips     |

Revision History

| Revision | Released | Remark          |
|----------|----------|-----------------|
| Rev.1.0  | 2024     | Initial Release |

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which requires high reliability. Customers using or selling these products for use in medical, life-saving, or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements, the information described or contained herein may be changed without prior notice.